REMARKS

Claims 1-29, 31, and 32 are pending in the application with claim 1 amended herein and claim 30 cancelled herein.

Page 5 of the Office Action states that claim 30 sets forth allowable subject matter. Claim 30 depended from claim 1 and claim 1 is herein amended incorporating the subject matter of claim 30. Accordingly, amended claim 1 is patentable over the cited art. Claims 2-9 depend from claim 1 and are further patentable at least for such reason as well as the additional limitations of such claims.

At least for the reasons set forth above, claims 1-29, 31, and 32 are in condition for allowance. Applicants request allowance of all pending claims in the next Office Action.

Respectfully submitted,

Dated: 21 Aug 2001

By: _____
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Application Serial No. 09/234,233
Filing Date ..... January 20, 1999
Inventor ..... Weimin Li, et al
Assignee ..... Micron Technology, Inc.
Group Art Unit 2818
Examiner ..... D. Vu
Attorney's Docket No. MI22-1035
Title: Semiconductor Processing Methods

VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING RESPONSE TO MAY 22, 2001 OFFICE ACTION

In the Claims

The claims have been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

1. (Once amended) A semiconductor processing method, comprising:

forming a layer of material comprising oxygen, as initially deposited, over a semiconductive wafer substrate;

exposing some portions of the layer to energy while leaving other portions unexposed, the exposing altering physical properties of the exposed portions of material relative to the unexposed portions of material;

after the exposing, subjecting the exposed and unexposed portions of the layer to common conditions, the common conditions being effective to remove the material and comprising a rate of removal that is influenced by the altered physical properties of the layer, the common conditions removing either the exposed or unexposed portions faster than the other of the exposed and unexposed portions; and

after the selective removal of the exposed or unexposed portions, and while the other of the exposed and unexposed portions remains over the substrate, cutting the wafer into separated die.

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